

Tatsuya Yamamoto

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3180656/publications.pdf>

Version: 2024-02-01

27
papers

506
citations

687220

13
h-index

677027

22
g-index

27
all docs

27
docs citations

27
times ranked

597
citing authors

#	ARTICLE	IF	CITATIONS
1	Recent Progress in the Voltage-Controlled Magnetic Anisotropy Effect and the Challenges Faced in Developing Voltage-Torque MRAM. <i>Micromachines</i> , 2019, 10, 327.	1.4	96
2	Enhancement in the interfacial perpendicular magnetic anisotropy and the voltage-controlled magnetic anisotropy by heavy metal doping at the Fe/MgO interface. <i>APL Materials</i> , 2018, 6, .	2.2	53
3	Voltage-controlled magnetic anisotropy in an ultrathin Ir-doped Fe layer with a CoFe termination layer. <i>APL Materials</i> , 2020, 8, .	2.2	40
4	Fully epitaxial C1b-type NiMnSb half-Heusler alloy films for current-perpendicular-to-plane giant magnetoresistance devices with a Ag spacer. <i>Scientific Reports</i> , 2016, 5, 18387.	1.6	38
5	Improvement of write error rate in voltage-driven magnetization switching. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 164001.	1.3	36
6	Write-Error Reduction of Voltage-Torque-Driven Magnetization Switching by a Controlled Voltage Pulse. <i>Physical Review Applied</i> , 2019, 11, .	1.5	32
7	Thermally Induced Precession-Orbit Transition of Magnetization in Voltage-Driven Magnetization Switching. <i>Physical Review Applied</i> , 2018, 10, .	1.5	29
8	Magnetoresistance effect in Fe ₂₀ Ni ₈₀ /graphene/Fe ₂₀ Ni ₈₀ vertical spin valves. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	22
9	Perpendicular magnetic anisotropy and its voltage control in MgO/CoFeB/MgO junctions with atomically thin Ta adhesion layers. <i>Acta Materialia</i> , 2021, 216, 117097.	3.8	19
10	Vortex spin-torque oscillator using $\text{Co}_2\text{Fe}_x\text{Mn}_{1-x}\text{Si}$ Heusler alloys. <i>Physical Review B</i> , 2016, 94, .	1.1	18
11	Reduction in the write error rate of voltage-induced dynamic magnetization switching using the reverse bias method. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 040311.	0.8	18
12	Voltage-Driven Magnetization Switching Using Inverse-Bias Schemes. <i>Physical Review Applied</i> , 2020, 13, .	1.5	18
13	Developments in voltage-controlled subnanosecond magnetization switching. <i>Journal of Magnetism and Magnetic Materials</i> , 2022, 560, 169637.	1.0	15
14	Voltage-Driven Magnetization Switching Controlled by Microwave Electric Field Pumping. <i>Nano Letters</i> , 2020, 20, 6012-6017.	4.5	14
15	Enhanced current-perpendicular-to-plane giant magnetoresistance effect in half-metallic NiMnSb based nanojunctions with multiple Ag spacers. <i>Applied Physics Letters</i> , 2016, 108, .	1.5	11
16	Enhancing the interfacial perpendicular magnetic anisotropy and tunnel magnetoresistance by inserting an ultrathin LiF layer at an Fe/MgO interface. <i>NPG Asia Materials</i> , 2022, 14, .	3.8	10
17	Accurate calculation and shaping of the voltage pulse waveform applied to a voltage-controlled magnetic random access memory cell. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 073002.	0.8	9
18	Recent progress in random number generator using voltage pulse-induced switching of nano-magnet: A perspective. <i>APL Materials</i> , 2021, 9, .	2.2	9

#	ARTICLE	IF	CITATIONS
19	Generation of charge current from magnetization oscillation via the inverse of voltage-controlled magnetic anisotropy effect. <i>Science Advances</i> , 2020, 6, eabc2618.	4.7	6
20	Characterization of spin pumping effect in Permalloy/Cu/Pt microfabricated lateral devices. <i>Journal of Applied Physics</i> , 2014, 115, 17C505.	1.1	3
21	Development of a high-sensitivity VNA-FMR spectrometer with field modulation detection and its application to magnetic characterization. <i>Electronics and Communications in Japan</i> , 2021, 104, e12320.	0.3	3
22	Perpendicular magnetic anisotropy and its voltage control in MgO/CoFeB/Mo/CoFeB/MgO junctions. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 275003.	1.3	3
23	Perpendicular magnetic anisotropy and its electrical control in FeNiB ultrathin films. <i>AIP Advances</i> , 2021, 11, .	0.6	2
24	High-speed write error rate evaluation of a voltage-torque magnetic random access memory cell. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 060905.	0.8	1
25	Improvement in perpendicular magnetic anisotropy and its voltage control efficiency in CoFeB/MgO tunnel junctions with Ta/Mo layered adhesion structures. <i>Journal of Applied Physics</i> , 2022, 131, 213901.	1.1	1
26	Observation and suppression of quantized spin waves in microfabricated permalloy elements. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 04EM01.	0.8	0
27	Perpendicular Magnetic Anisotropy and its Voltage Control in MgO/CoFeB/MgO Junctions with Atomically Thin Ta Adhesion Layers. <i>SSRN Electronic Journal</i> , 0, , .	0.4	0